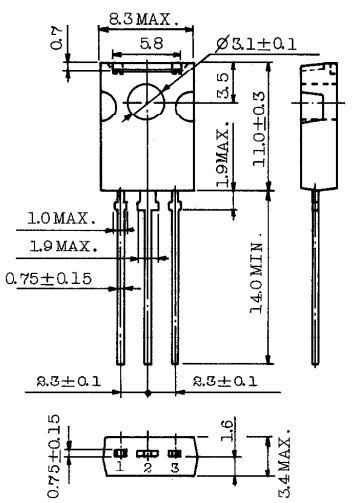
TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

2SA1358

AUDIO FREQUENCY POWER AMPLIFIER APPLICATIONS.

Unit in mm

- Complementary to 2SC3421
- Suitable for Driver of 60 to 80 Watts.
- High Breakdown Voltage.



1. EMITTER
2. COLLECTOR
3. BASE

JEDEC	—
EIAJ	—
TOSHIBA	2-8H1A

Weight : 0.82g

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	−120	V
Collector-Emitter Voltage		V_{CEO}	−120	V
Emitter-Base Voltage		V_{EBO}	−5	V
Collector Current		I_C	−1	A
Base Current		I_B	−100	mA
Collector Power Dissipation	Ta = 25°C	P_C	1.5	W
	Tc = 25°C		10	
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	−55~150	°C

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

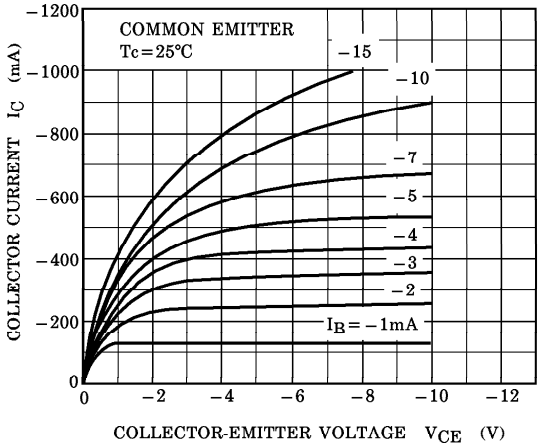
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB} = −120V, I_E = 0	—	—	−100	nA
Emitter Cut-off Current	I_{EBO}	V_{EB} = −5V, I_C = 0	—	—	−100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = −10mA, I_B = 0	−120	—	—	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E = −1mA, I_C = 0	−5	—	—	V
DC Current Gain	h_{FE} (Note)	V_{CE} = −5V, I_C = −100mA	80	—	240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = −500mA, I_B = −50mA	—	−0.40	−1.0	V
Base-Emitter Voltage	V_{BE}	V_{CE} = −5V, I_C = −500mA	—	−0.77	−1.0	V
Transition Frequency	f_T	V_{CE} = −5V, I_C = −100mA	—	120	—	MHz
Collector Output Capacitance	C_{ob}	V_{CB} = −10V, I_E = 0, f = 1MHz	—	30	—	pF

Note : h_{FE} Classification O : 80~160, Y : 120~240

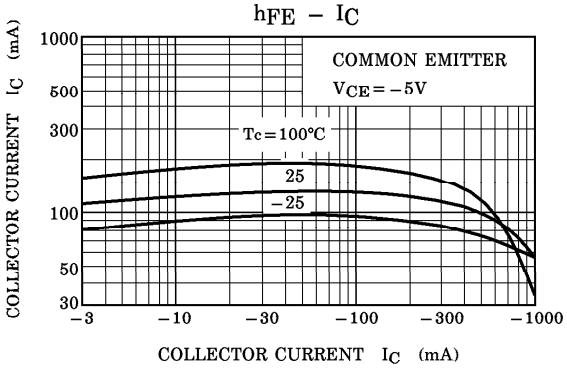
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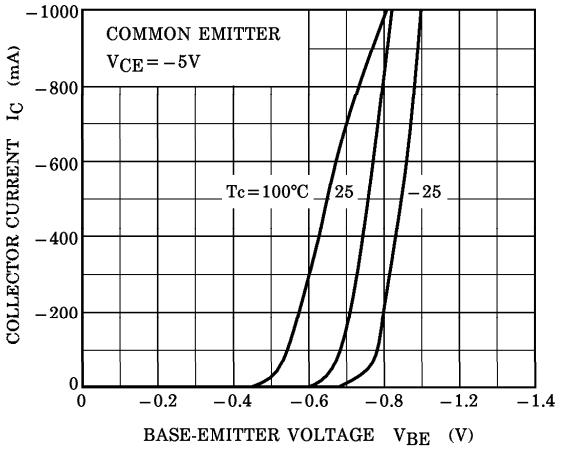
$I_C - V_{CE}$



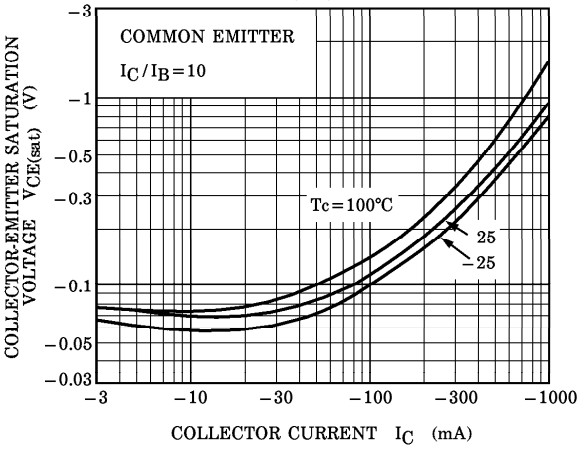
$h_{FE} - I_C$



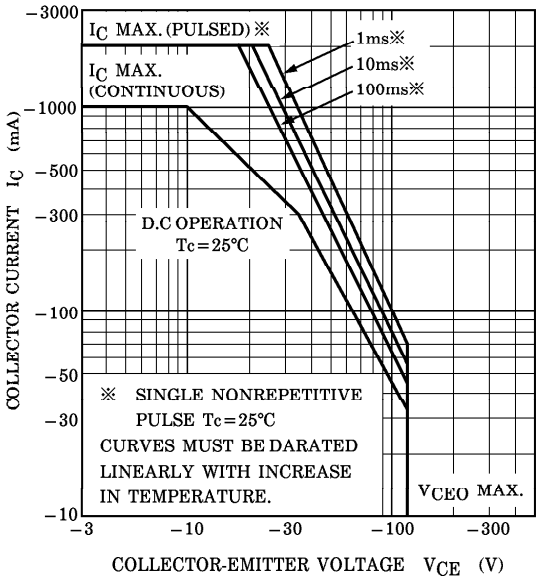
$I_C - V_{BE}$



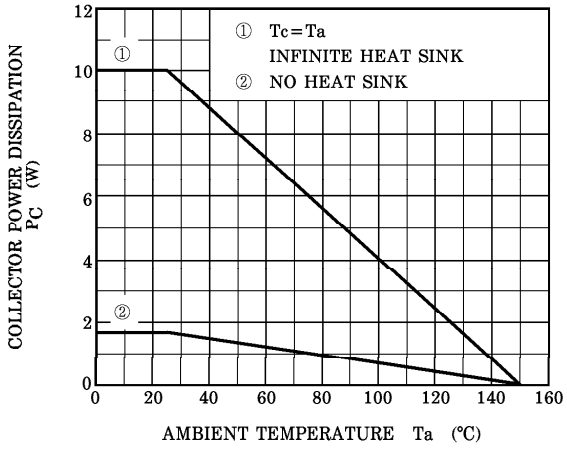
$V_{CE(sat)} - I_C$



SAFE OPERATING AREA



$P_C - Ta$



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